

AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph on page 11, line 9 with the following amended paragraph:

In the third embodiment, the seed crystal 3 having a hexagonal shape is used. The direction defined by a vertex and a diagonal vertex of the hexagon is $\langle 11\bar{2}0 \rangle$. The plane direction of the crystal 3 is (0001). The seed crystal 3 is supported by three hook-shaped members 7 at the vicinity of vertices of the hexagon where crystal growth rate is the fastest in the expanding direction. Therefore, the SiC single crystal 4 is not unfavorably prevented from expanding in the diameter direction, the protection layer 5 on the back surface of the SiC seed crystal 3 is not damaged, and macroscopic defects are suppressed. Thus, a high-quality, long SiC single crystal 4 is formed. In addition, circular SiC wafers are efficiently cut out of the polygonal grown crystal, and an SiC single crystal having a large diameter is provided.